

Publications

2001

Energy band structure of Zn_3P_2 -type semiconductors: analysis of the crystal structure simplifications and energy band calculations

J. Andrzejewski, J. Misiewicz

Physica Status Solidi B **227**, 515 (2001)

Excitons at the p-type modulation doped $\text{Al}_{0.5}\text{Ga}_{0.5}\text{As}/\text{GaAs}$ interface

L. Bryja, K. Ryczko, M. Kubisa, J. Misiewicz, O. Stern, M. Bayer, A. Forchel, C. B. Sorensen

Proceedings of the SPIE, **4413** 16 (2001)

Optical and structural characterization of erbium-doped TiO_2 xerogel films processed on porous anodic alumina

N. V. Gaponenko, O. V. Sergeev, E. A. Stepanova, V. M. Parkun, A. V. Mudryi, H. Gnaser, J. Misiewicz, R. Heiderhoff, L. J. Balk, G. E. Thompson

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Terbium photoluminescence in polysiloxane films

N.V. Gaponenko, O.V. Sergeev, V.E. Borisenko, J.C. Pivin, P. Skeldon, G.E. Thompson, B. Hamilton, J. Misiewicz, L. Bryja, R. Kudrawiec, A.P. Stupak, E.A. Stepanova

Materials Science & Engineering B Solid State Materials for Advanced Technology **B81**, 191 (2001)

Optical properties of GaN layers grown by MOCVD

R. Kudrawiec, L. Bryja, J. Misiewicz, R. Paszkiewicz, R. Korbutowicz, M. Panek, H. Paszkiewicz, M. Tłaczała

Proceedings of the SPIE, **4413** 37 (2001)

MOVPE GaN grown on alternative substrates

R. Paszkiewicz, B. Paszkiewicz, R. Korbutowicz, J. Kozłowski, M. Tłaczała, L. Bryja, R. Kudrawiec, J. Misiewicz

Crystal Research and Technology **36**, 971 (2001)

Giant absorption of light in quasi-zero-dimensional structures

S. I. Pokutnyi, L. Jacak, J. Misiewicz, W. Salejda, M.H. Tyc

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Two-dimensional Wannier-Mott exciton in an uniform electric field

S. Pokutnyi, M.H. Tyc, W. Salejda, J. Misiewicz

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Photoreflectance spectroscopy of vertically coupled InGaAs/GaAs double quantum dots

G. Sęk, K. Ryczko, J. Misiewicz, M. Bayer, F. Klopff, J. P. Reithmaier, A. Forchel
Solid State Communications **117**, 401 (2001)

Coupled In_{0.6}Ga_{0.4}As/GaAs quantum dots: a photoreflectance study

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Proceedings of the SPIE, **4413** 139 (2001)

Influence of built-in electric field on forbidden transitions in In_xGa_{1-x}As/GaAs double quantum well by three-beam photoreflectance

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Acta Physica Polonica A **100**, 417 (2001)

Photoreflectance investigations of GaN epitaxial layers

P. Sitarek, R. Kudrawiec, G. Sęk, J. Misiewicz, R. Paszkiewicz, R. Korbutowicz, B. Paszkiewicz, M. Tłaczała
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Epitaxial growth and characterisation of silicon delta-doped GaAs, AlAs and Al_xGa_{1-x}As

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Photoreflectance investigation of delta-doped MOVPE-grown Al_xGa_{1-x}As layers

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